

# ABSTRACT OF THE DISCLOSURE

5 A semiconductor device includes a substrate,  
a well region formed in the substrate, a field effect  
transistor formed in the well region, and a diffused  
region, formed across the well region and the substrate  
for applying back gate potential to the well region,  
and forming a PN junction together with its periphery.  
The field effect transistor and the PN junction are  
10 connected between terminals for absorbing excess  
current so that an internal circuit connected to the  
terminals is protected.